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CLAIMS -

- 1. A chamber cleaning gas comprising at least one gas selected from the group consisting of $CF_3CF=CF_2$, CF_3CF-CF_2 and $CF_3C=0$.
- 2. A chamber cleaning gas according to claim 1 comprising CF₃CF=CF₂.
- 3. A chamber cleaning gas according to claim 1 comprising hexafluoropropylene oxide represented by the formula CF₃CF-CF₂.
- 4. A chamber cleaning gas according to claim 1 comprising CF₃COCF₃.
- A chamber cleaning gas according to any one of

 Claims 1-4 which further comprises at least one monomer

 gas selected from the group consisting of He, Ne, Ar, H₂,

 N₂ and O₂.
 - 6. A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one chamber cleaning gas selected from the group consisting of CF₃CF=CF₂, CF₃CF-CF₂ and CF₃C=0.
- 7. A chamber cleaning method according to claim 6
 25 wherein the chamber cleaning gas is CF₃CF=CF₂.

- 8. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is hexafluoropropylene oxide represented by the formula ${\rm CF_3CF-CF_2}$.
- 9. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is CF₃COCF₃. A chamber cleaning gas according to any one of claims 6-9 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H₂, and O₂.

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